JST12i Series 12A TRIACs

DESCRIPTION:

High current density due to double mesa technology; SIPOS and Glass Passivation.

JST12i series triacs is suitable for general purpose AC switching. They can be used as an ON/OFF Function in applications such as static relays, heating regulation, induction motor stating circuits... or for phase contol operation light dimmers, motorspeed controllers.

JST12i-×××TW、-×××SW、-×××CW 、-×××BW are 3 Quadrants triacs, They are specially recommended for use on inductive loads.

JST12i are isolated internally, they provides a 2500V RMS isolation voltage from all three terminals to extemal heetsink.

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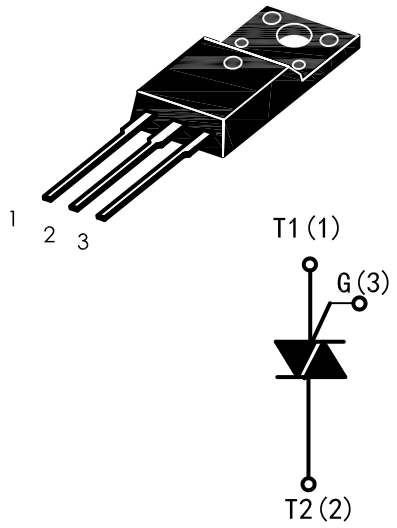


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	600and800	V
V_{TM}	≤1.55	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range Operrating junction temperature range		Tstg Tj	-40 to +150 -40 to +125	℃
Repetitive Peak Off-state Voltage Repetitive Peak Reverse Voltage	Tj=25℃	V_{DRM} V_{RRM}	600and800 600and800	V
Non repetitive Surge Peak Off-state Voltage Non repetitive Peak Reverse Voltage	Tj=25℃	V_{DSM} V_{RSM}	700and900 700and900	V
RMS on-state current (full sine wave)	T_C=79℃	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle, Tj=25℃)	f = 50 Hz t=20ms f = 60 Hz t=16.7ms	I_{TSM}	120 126	A
I^2t Value for fusing	tp=10ms	I^2t	78	A^2s
Critical rate of rise of on-state current I_G=2×I_{GT}, tr≤100 ns, f=120Hz, Tj=125℃		dI /dt	50	A/us
Peak gate current	tp=20us, Tj=125℃	I_{GM}	4	A
Average gate power dissipation	Tj=125℃	$P_{G(AV)}$	1	W

ELECTRICAL CHARACTERISTICS(Tj=25℃ unless otherwise specified)

● 3 Quadrants

Symbol	Test Condition	Quadrant		JST12i				Unit
				TW	SW	CW	BW	
I_{GT}	V_D=12V R_L=30Ω	I - II - III	MAX.	5	10	35	50	mA
V_{GT}		I - II - III	MAX.	1.3				V
V_{GD}	V_D=V_{DRM} R_L=3.3KΩ Tj=125℃	I - II - III	MIN..	0.2				V
I_L	I_G=1.2I_{GT}	I - III	MAX.	10	25	50	70	mA
		II		15	30	60	80	
I_H	I_T=100mA		MAX.	10	15	35	50	mA
dV/dt	V_D=67%V_{DRM} gate open Tj=125℃		MIN.	20	40	500	1000	V/μs
(dI/dt)c	(dV/dt) c=0.1V/μs Tj=125℃		MIN.	3.5	6.5	----	----	A/ms
	(dV/dt) c=10V/μs Tj=125℃			1.0	2.9	----	----	
	Without snubber Tj=125℃			----	----	6.5	12	

● 4 Quadrants

Symbol	Test Condition	Quadrant		JST12i		Unit
				C	B	
I_{GT}	V_D=12V R_L=30Ω	I - II - III IV	MAX.	25 50	50 100	mA
V_{GT}		ALL	MAX.	1.3		V
V_{GD}	V_D=V_{DRM} R_L=3.3KΩ Tj=125℃	ALL	MIN.	0.2		V
I_L	I_G=1.2I_{GT}	I - III - IV	MAX.	40	50	mA
		II		80	100	
I_H	I_T=100mA		MAX.	25	50	mA
dV/dt	V_D=67%V_{DRM} gate open Tj=125℃		MIN.	200	400	V/μs
(dI/dt)c	(dV/dt) c=0.1V/μs Tj=125℃		MIN.	----	----	
	(dV/dt) c=10V/μs Tj=125℃			----	----	
	Without snubber Tj=125℃			----	----	

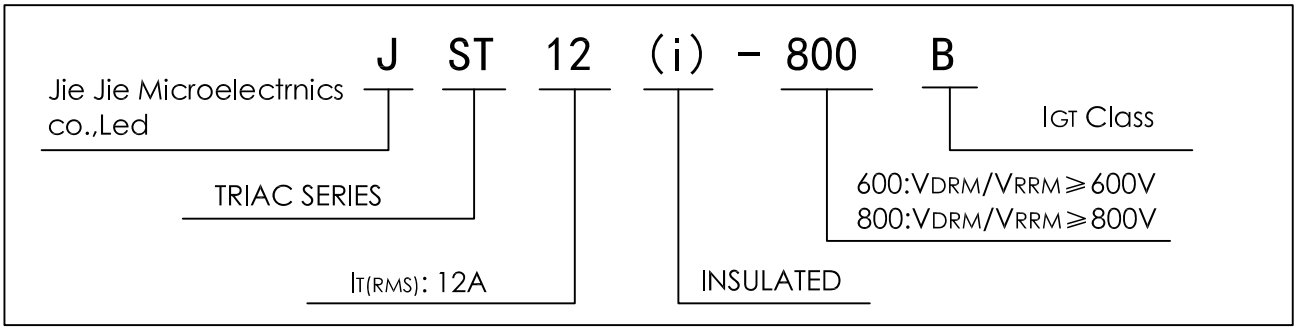
STATIC CHARACTERISTICS

Symbol	Test Conditions		Value (MAX)	Unit
V_{TM}	I_{TM}=17A, tp=380uS	Tj=25℃	1.55	V
I_{DRM}	$V_D=V_{DRM}$	Tj=25℃	5	uA
I_{RRM}	$V_R=V_{RRM}$	Tj=125℃	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	3.3	℃/W

ORDERING INFORMATION



PACKAGE MECHANICAL DATA

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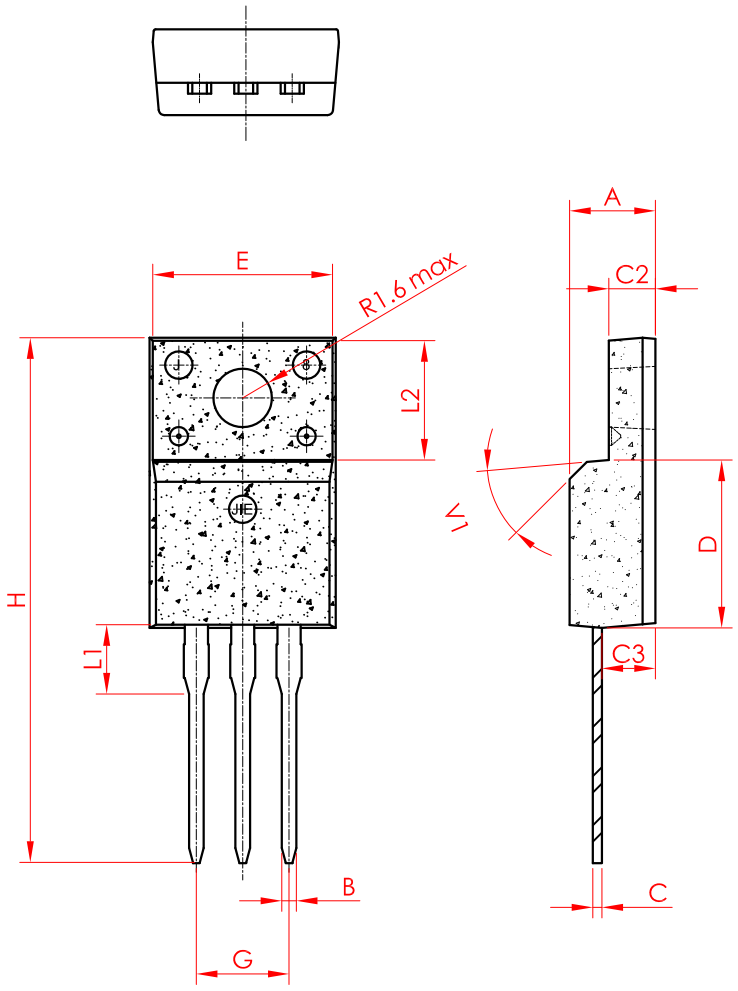

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.3		4.7	0.169		0.185
B	0.74	0.8	0.83	0.029	0.031	0.033
C	0.5		0.75	0.020		0.030
C2	2.4		2.7	0.094		0.106
C3	2.5		2.9	0.098		0.114
D	8.6		9.2	0.338		0.362
E	9.7		10.3	0.382		0.406
G	5.0		5.2	0.197		0.205
H	28.0		29.8	11.0		11.7
L1		3.63			0.143	
L2	6.3		6.5	0.136		0.143
V1		40°			40°	

Fig. 1: Maximum power dissipation versus RMS on-state current(full cycle)

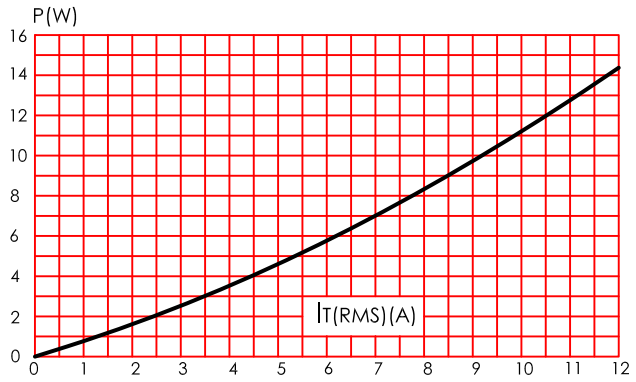

Fig. 2: RMS on-state current versus case temperrature(full cycle)

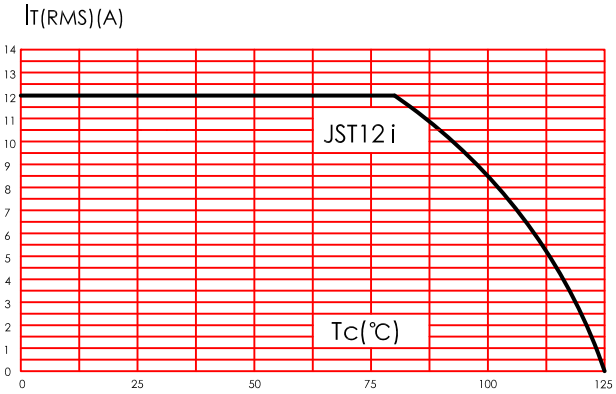

Fig. 3: on-state characteristics (maximum values)

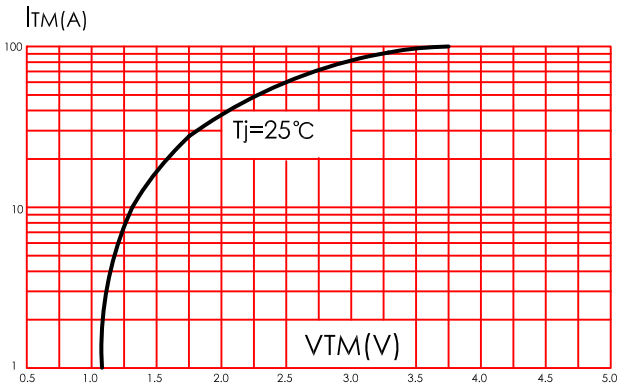

Fig. 4: Surge peak on-state current versus number of cycyles

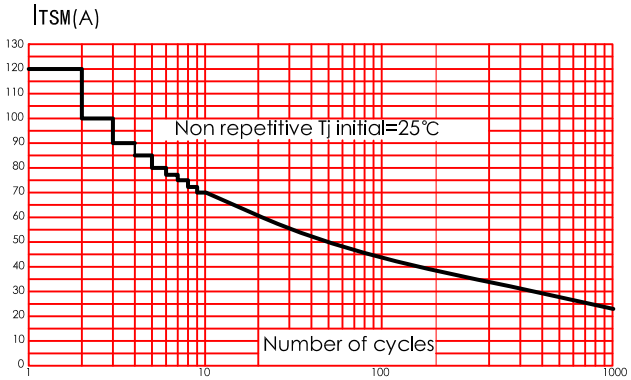

Fig. 5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10mS

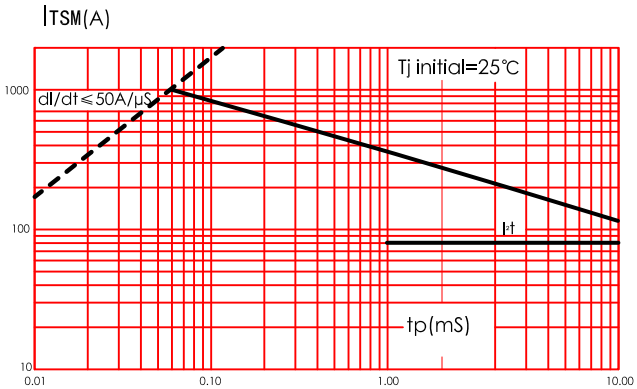

Fig. 6: **Relative variation** of gate trigger currunt, holding current and latching current versus junction temperature(typical values)